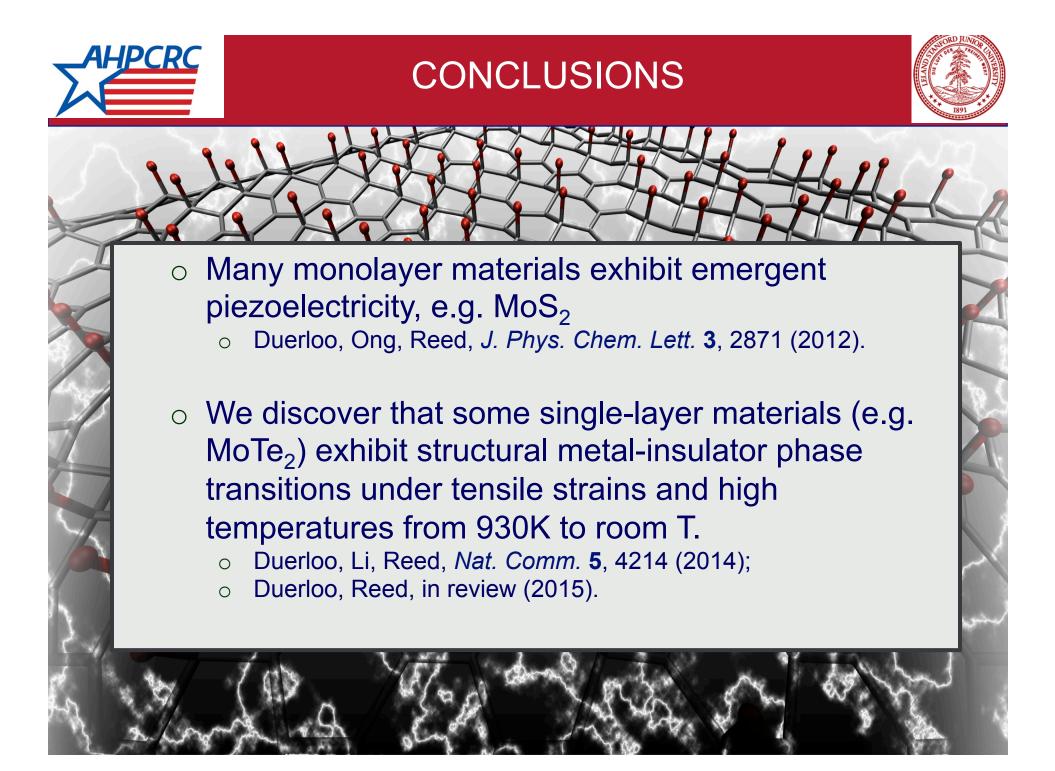




### Phase Change and Piezoelectric Properties of Two-Dimensional Materials

### April 16, 2015 Karel-Alexander Duerloo, Yao Li, Yao Zhou, Evan Reed Department of Materials Science and Engineering Stanford University







### PIEZOELECTRIC MATERIAL APPLICATIONS

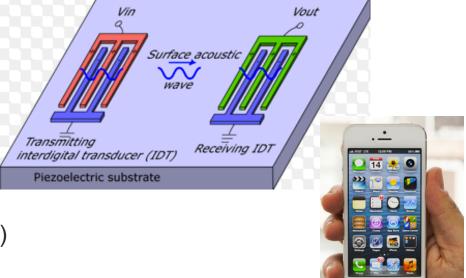


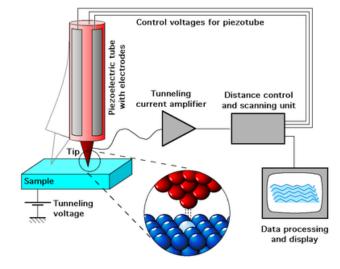
### **Stress Sensors**



### Scanning Tunneling Microscope (STM)

Acoustic transducers for signal processing





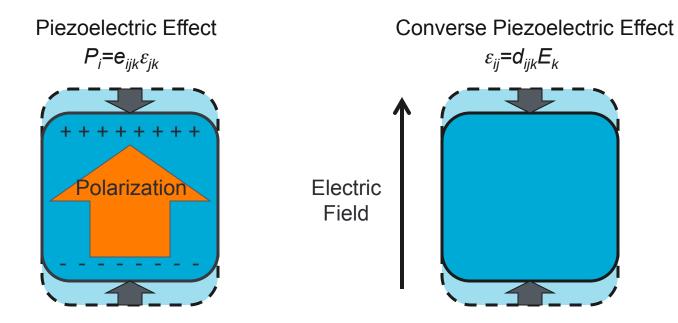
**Injet Printing** 





# PIEZOELECTRICITY





Piezoelectric materials must exhibit:

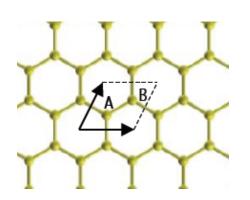
- 1. An electronic bandgap
- 2. A lack of centrosymmetry

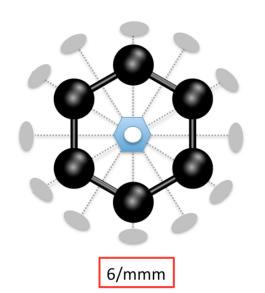
Inversion symmetry of a crystal =>  $d_{ijk} = (-1)^3 d_{ijk} = -d_{ijk}$ So  $d_{ijk}=0$  for crystals with inversion symmetry!





# graphene





- Inversion symmetry => non-piezoelectric
- Semi-metallic character => nonpiezoelectric

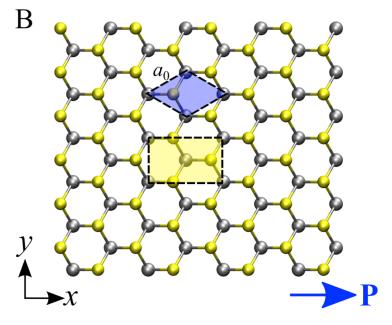


Transition Metal Dichalcogenides: MoS<sub>2</sub>, MoSe<sub>2</sub>. MoTe<sub>2</sub>, WS<sub>2</sub>, WSe<sub>2</sub>

Trigonal prismatic structure:

- Semiconducting (E<sub>gap</sub> ~ 1-2 eV)
- Not centrosymmetric
  - ✓ 3m point group leads to non-zero  $d_{11}$  and  $e_{11}$  coefficients

$$\begin{bmatrix} \varepsilon_{xx} \\ \varepsilon_{yy} \\ \varepsilon_{xy} \end{bmatrix} = \begin{bmatrix} d_{11} & 0 & 0 \\ -d_{11} & 0 & 0 \\ 0 & -d_{11} & 0 \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix}$$



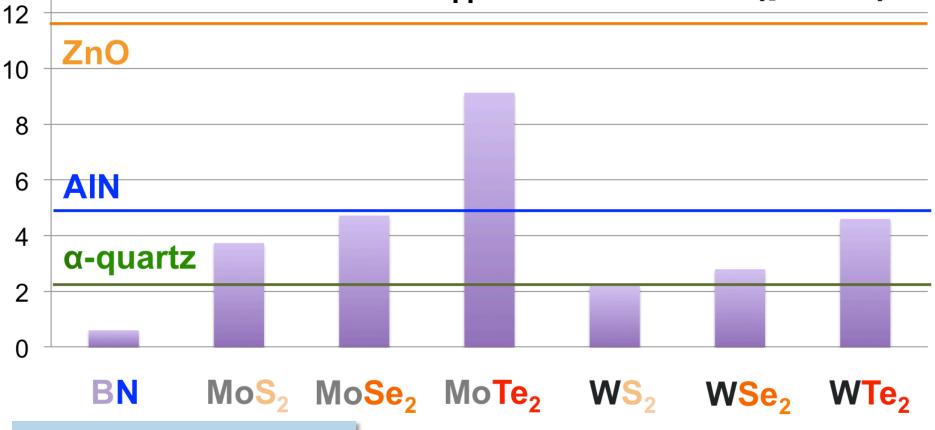
D

 $\varepsilon$ 

# WE DISCOVER THAT A VARIETY OF TMDS HAVE SIGNIFICANT PIEZOELECTRIC EFFECTS



# Calculated $d_{11}$ coefficients (pm/V)



Piezo-coefficients of trigonal prismatic TMD structures are comparable to bulk wurtzite structures

K.-A. Duerloo, M. T. Ong, E. J. Reed., J. Phys. Chem. Lett. 3, 2871 (2012).

### PIEZOELECTRICITY IN 2D MATERIALS HAS RECENTLY BEEN OBSERVED

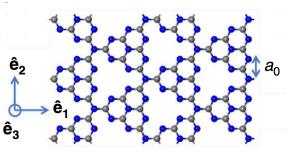


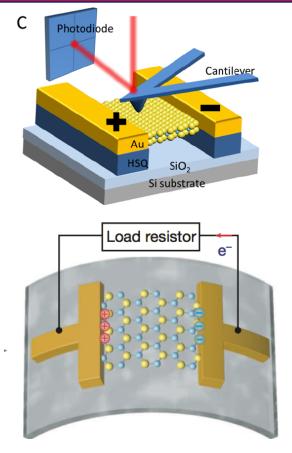
"Observation of Piezoelectricity in monolayer MoS<sub>2</sub>," Zhu, Wang, Xiao, Liu, Xiong, Wong, Ye, Yin, Zhang, *Nature Nanotechnology (2014).*Reported e<sub>11</sub> within 20% of predicted.

"Piezoelectricity of single atomic layer MoS<sub>2...</sub>" Wu, Wang, Hone, Wang *et al.*, *Nature* (2014).

### Piezoelectricity in

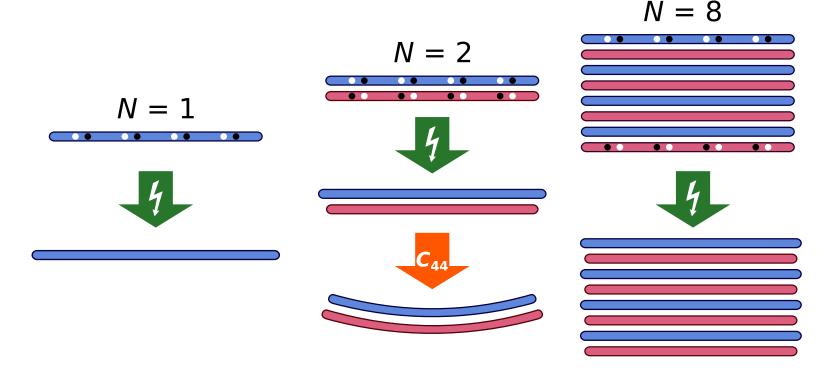
**C**<sub>3</sub>**N**<sub>4</sub> **few layers**: Zelisko, *et al,* Nature Communications (2014).







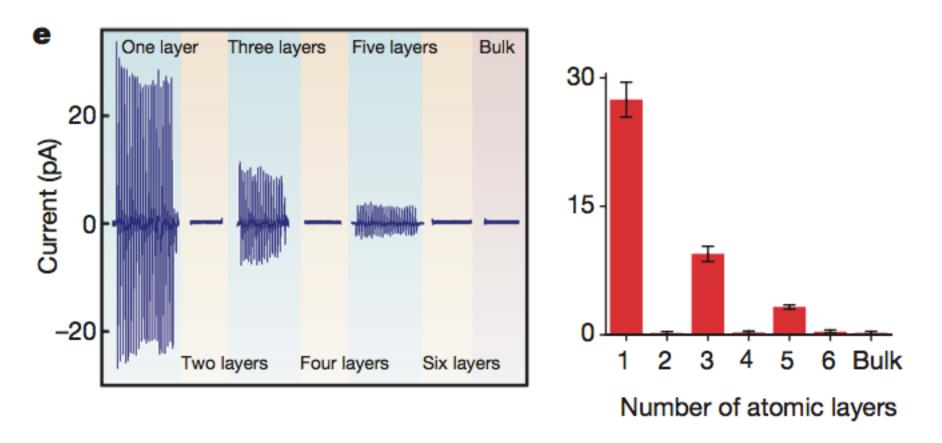
We find that TMDC monolayers are piezoelectric while their bulk host crystals exhibit an inversion center and are therefore not piezoelectric!



We predict bilayer BN exhibits an electromechanical curvature effect.

K.-A. Duerloo, E. J. Reed., Nano Letters (2013).

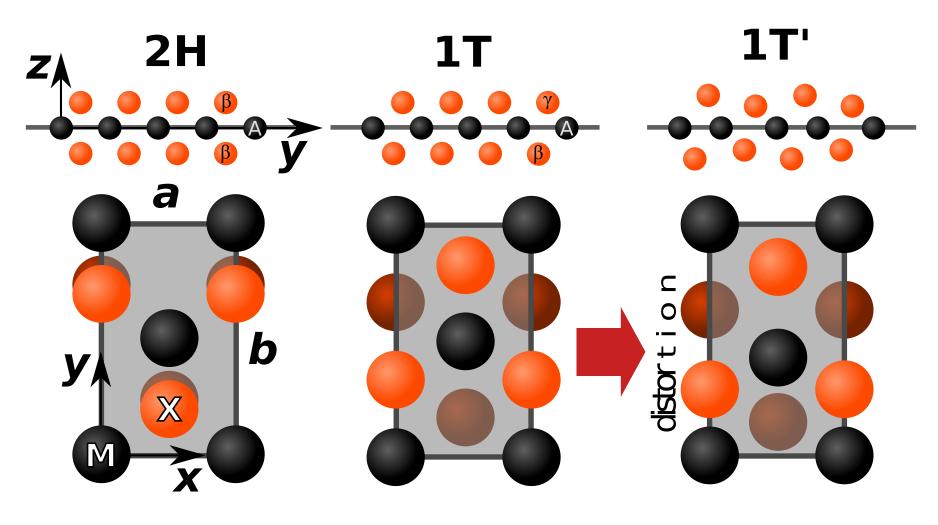
### PIEZOELECTRIC EFFECTS OBSERVED ONLY FOR ODD NUMBERS OF LAYERS



**Piezoelectricity of single atomic layer MoS<sub>2...</sub>**" Wu, Wang, Hone, Wang *et al.*, *Nature* (2014).







Semiconducting (1-2 eV)

AH<u>PCRC</u>

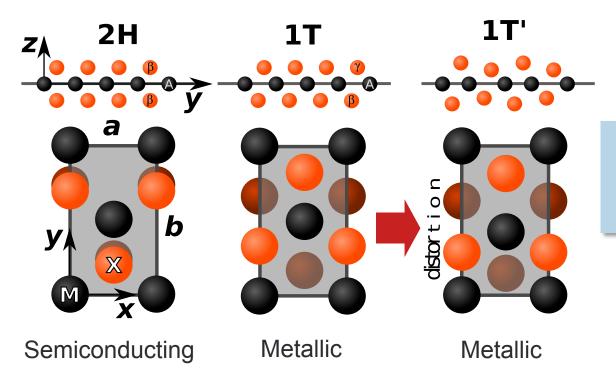
Metallic

Semi-metallic



# TMD MONOLAYERS MIGHT EXIST IN MULTIPLE CRYSTAL STRUCTURES

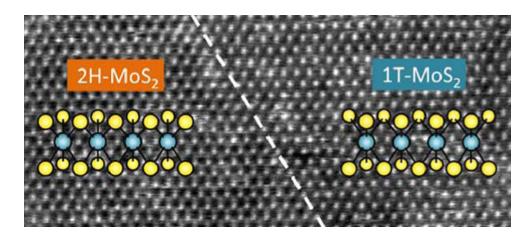




Can the phases of monolayers be engineered and employed in devices?

Two phases have been observed in chemically exfoliated  $MoS_2$  and  $WS_2$ .

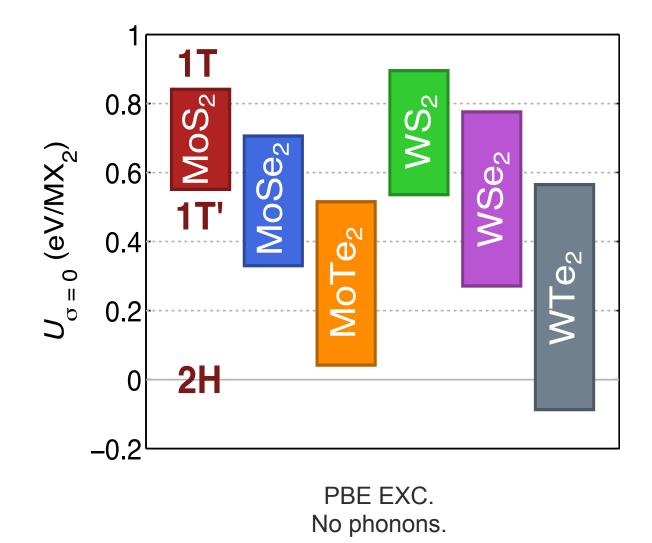
Eda et al, ACS Nano 6, 7311 (2012); Voiry et al, Nat. Mat. (2013).



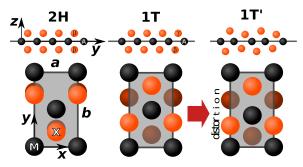


### MoTe<sub>2</sub> AND WTe<sub>2</sub> EXHIBIT PHASE BOUNDARIES NEAREST AMBIENT





Our semi-local DFT calcualtions indicate MoTe<sub>2</sub> and WTe<sub>2</sub> exhibit the smallest 2H-1T' energy difference.







# semiconductor

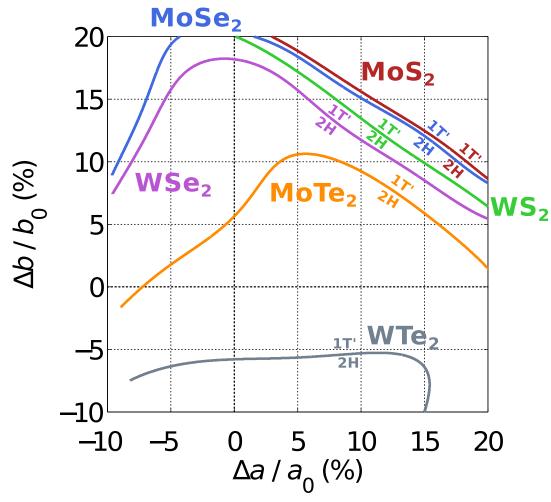




# WE COMPUTE STRAIN PHASE BOUNDARIES FOR MONOLAYERS

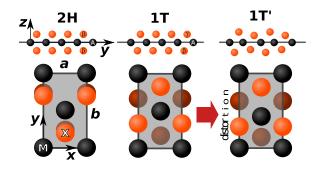


Our DFT/PBE calculations of TMD monolayer phase boundaries in strain.



Energy calculations on a 5x5 grid in (a,b) lattice constants. Lagrange interpolation for phase boundaries.

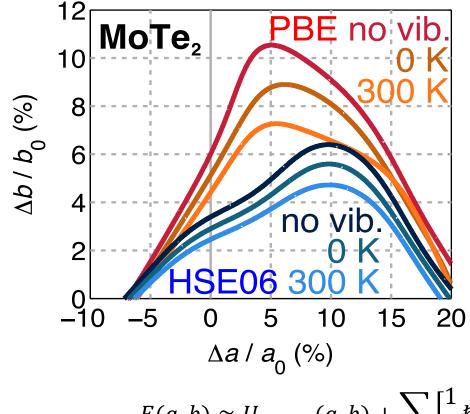
Tensile strain of 6% along b axis croses phase boundary in  $MoTe_2$ .



Duerloo, Li, Reed, Nature Communications, (2014).

### HYBRID EXCHANGE AND ENTROPIC AH<u>PCRC</u> EFFECTS IMPACT MoTe<sub>2</sub> BOUNDARY





- Hybrid exchange (HSE06) moves phase boundary closer to ambient conditions
- Incorporation of entropic effects (F=E-TS) accomplished using quasiharmonic approximation with computed phonon bands

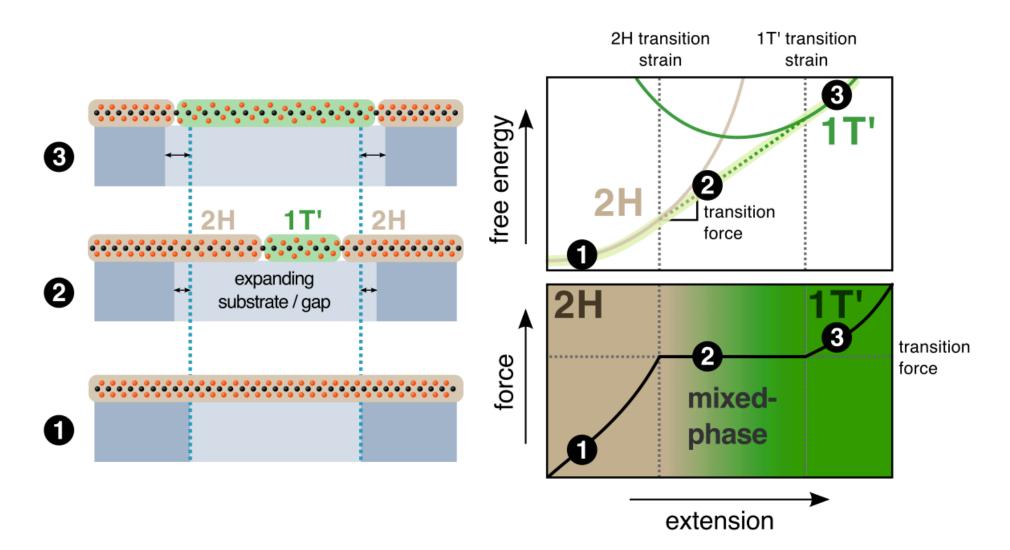
$$F(a,b) \approx U_{\text{crystal}}(a,b) + \sum_{i} \left[ \frac{1}{2} \hbar \omega_{i}(a,b) + k_{\text{B}} T \ln \left( 1 - e^{-\hbar \omega_{i}(a,b)/k_{\text{B}} T} \right) \right]$$

HSE06 with room T vibrations predict phase boundary within 3% tensile strain in  $MoTe_2$ .



### STRAIN INDUCED STRUCTURAL TRANSITION FROM 2H TO 1T'





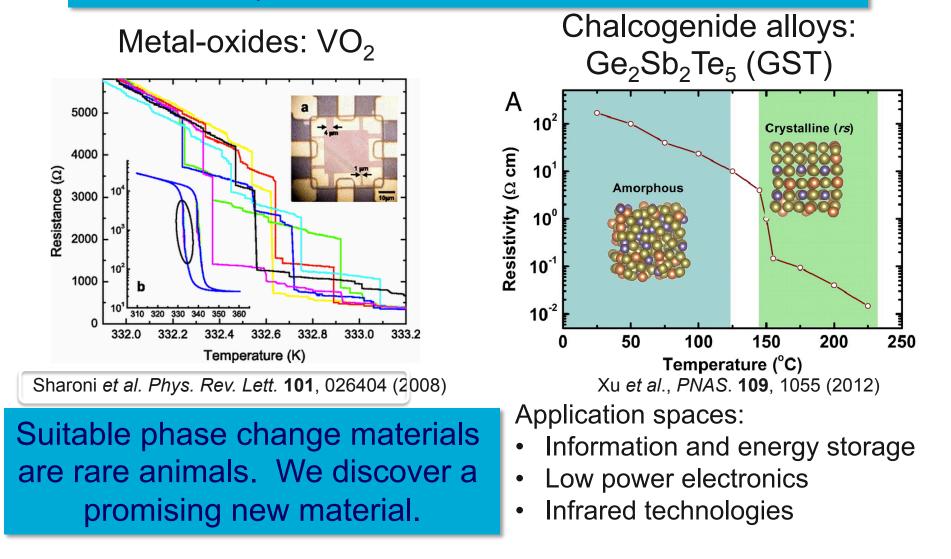
Duerloo, Li, Reed, Nature Communications, (2014).



# CONTEXT: PHASE CHANGE MATERIALS FOR ELECTRONICS



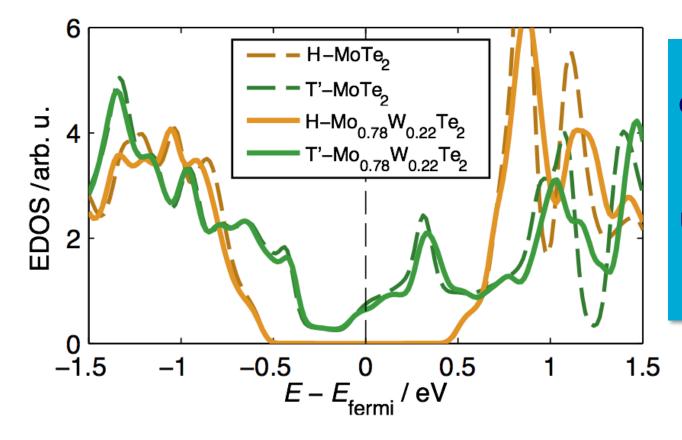
New materials are needed to mitigate escalating power requirements for electronic devices.







Kohn-Sham (single particle) electronic density of states for H and T' MoTe.



Large predicted electronic changes across the phase transition provide utility for electronic and infrared devices.

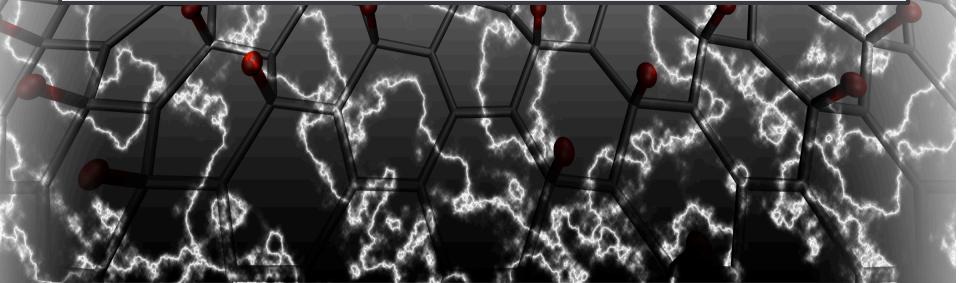
Duerloo, Reed, in review (2015).



### METROLOGY NEEDS



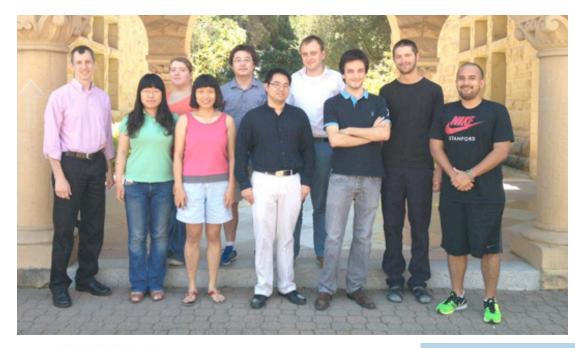
- Number of layers
- Crystal structure
- $\circ~$  Point defects for TMDs
- Chemical composition for alloys





### ACKNOWLEDGEMENTS



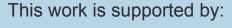


Karel-Alexander Duerloo Mitchell Ong Yao Li Yao Zhou









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